

Insulated Gate Bipolar Transistor, IGBT

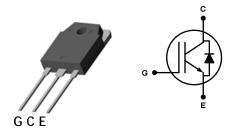
## 1200V, 15A High Speed Field Stop IGBT

#### **Features**

- Low gate charge
- Field Sotp Technology
- Low saturation voltage:  $V_{CE(sat)} = 1.8V$  (@  $I_C = 15A$ ,  $T_C = 25^{\circ}C$ )
- RoHS compliant product

#### **Applications**

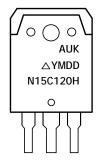
- General purpose inverters
- Induction heating (IH)
- UPS



TO-247

#### **Ordering Information**

Part Number	Marking	Package
SGTN15C120HW	N15C120H	TO-247



Column 1: Manufacturer

Column 2: Production Information

e.g.) △YMDD

-. △: Factory Management Code

-. YMDD: Date Code (Year, Month, Daily)

Column 3: Device Code

#### Absolute Maximum Ratings (T<sub>c</sub>=25°C unless otherwise noted)

Characteristic	Symbol		Rating	Unit		
Collector-emitter voltage	V <sub>CES</sub>		V <sub>CES</sub>		1200	٧
Continuous collector current (1)		T <sub>c</sub> =25°C	30	А		
Continuous cottector current	I <sub>C</sub>	T <sub>c</sub> =100°C	15	А		
Pulsed collector current (2)		I <sub>CM</sub>	45	А		
Gate-emitter voltage		$V_{GES}$	±20	٧		
Turn-off safe area		-	45	А		
Power dissipation		P <sub>D</sub>	150	W		
Operating and storage temperature range		$T_{J_1}T_{stg}$	-55 to 150	°C		
Maximum lead temperature for soldering purpose	TL		300	°C		

<sup>1)</sup> Collector current limited by maximum junction temperature

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<sup>&</sup>lt;sup>2)</sup> Pulse width limited by maximum junction temperature and turn-off within RBSOA.

### Electrical Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

Characteristic	Symbol	Test Condition	Min.	Тур.	Max.	Unit	
Off-Characteristics							
Collector-emitter breakdown voltage	BV <sub>CES</sub>	I <sub>C</sub> =500uA, V <sub>GS</sub> =0	1200	-	-	٧	
Breakdown voltage temperature coefficient	△BV <sub>CES</sub> /△T <sub>J</sub>	I <sub>C</sub> =1mA, reference to 25°C	-	0.6	-	V/°C	
	I <sub>CES</sub>	$V_{CE}$ =1200V, $V_{GS}$ =0V, $T_{C}$ =25°C	-	-	0.2	mA	
Zero gate voltage collector current		V <sub>CE</sub> =1200V, T <sub>C</sub> =100°C	-	ı	2	mA	
		V <sub>CE</sub> =1200V, T <sub>C</sub> =150°C	-	-	2.5	mA	
Gate-body leakage current	I <sub>GSS</sub>	$V_{DS}$ =0V, $V_{GS}$ =±20V	-	-	±100	nA	
On-Characteristics							
Gate threshold voltage	$V_{GE(th)}$	V <sub>CE</sub> =V <sub>GE</sub> , I <sub>C</sub> =600uA	4.5	-	6.5	٧	
		V <sub>GE</sub> =15V, I <sub>C</sub> =15A	-	1.8	2.4	٧	
Collector-emitter saturation voltage	$V_{CE(sat)}$	V <sub>GE</sub> =15V, I <sub>C</sub> =50A, T <sub>C</sub> =150°C	-	2.1	-	٧	
Short collector current (3)	I <sub>C(SC)</sub>	V <sub>GE</sub> =15V,V <sub>CE</sub> =600V, t <sub>sc</sub> < 10us, T <sub>C</sub> =150°C	-	160	-	Α	
Dynamic-Characteristics			l				
Input capacitance	C <sub>ies</sub>		-	1500	2000		
Output capacitance	C <sub>oes</sub>	$V_{CE}$ =25V, $V_{GE}$ =0V, $f$ =1MHz	-	100	160	pF	
Reverse transfer capacitance	C <sub>res</sub>		-	70	110		
Turn-on delay time (4),(5)	t <sub>d(on)</sub>		-	30	-		
Rise time (4),(5)	t <sub>r</sub>		-	100	-	ns	
Turn-off delay time (4),(5)	t <sub>d(off)</sub>		-	100	-		
Fall time (4),(5)	t <sub>f</sub>	$V_{CE}$ =600V, $I_{C}$ =15A, $R_{G}$ =56 $\Omega$ , Inductive Load	-	150	-		
Turn-on energy (4),(5)	E <sub>on</sub>		-	1.5	-		
Turn-off energy (4),(5)	E <sub>off</sub>		-	0.9	-	mJ	
Total switching energy (4),(5)	E <sub>total</sub>		-	2.4	-	•	
Total gate charge (4),(5)	Qg	V <sub>CE</sub> =600V, V <sub>GE</sub> =15V, I <sub>C</sub> =15A	-	100	-	nC	

<sup>&</sup>lt;sup>3)</sup> Allowed number of short circuit: <1000; time between short circuit: >1s. <sup>4)</sup> Pulse test: Pulse width≤300us, Duty cycle≤2% <sup>5)</sup> Essentially independent of operating temperature typical characteristics

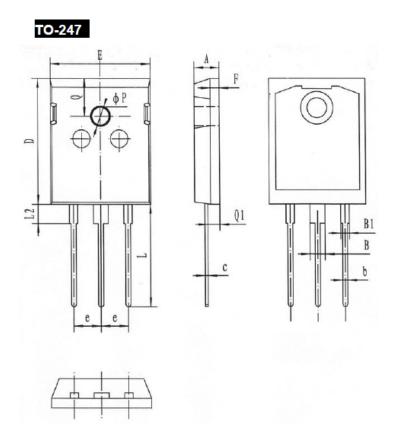
## Anti-Parallel Diode Characteristics and Maximum Ratings (T<sub>C</sub>=25°C unless otherwise noted)

Characteristic	Symbol	Test Condition	Min.	Тур.	Max.	Unit
Forward on voltage	$V_{F}$	V <sub>GE</sub> =0V, I <sub>F</sub> =15A	-	-	2.9	٧
Reverse recovery time (4),(5)	t <sub>rr</sub>	I <sub>F</sub> =10A, V <sub>GE</sub> =0V, V <sub>R</sub> =800V	-	150	-	ns
Reverse recovery charge (4),(5)	$Q_{rr}$	$dI_F/dt=750A/us$	-	1.2	-	uC

### **Thermal Characteristics**

Characteristic	Symbol	Rating	Unit
Thermal resistance, junction to case	$R_{th(j-c)}$	Max. 0.6	°C/W
Thermal resistance, junction to ambient	$R_{th(j\text{-}a)}$	Max. 40	C/ W

## Package Outline Dimensions



### 单位 Unit: mm

MIN	MAX
4.90	5.10
2.85	3.11
1.95	2.05
1.15	1.25
0.60	TYP
20.77	21.07
15.77	16.03
5.32	5.58
1.92	2.08
20.05	20.31
4.22	4.32
6.00	6.20
2.33	2.43
3.65	3.75
	2.85 1.95 1.15 0.60 20.77 15.77 5.32 1.92 20.05 4.22 6.00 2.33

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